

## Product Summary

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> max T <sub>A</sub> = +25°C
-12V	14.8mΩ @ V <sub>GS</sub> = -4.5V	-9.5A
	19mΩ @ V <sub>GS</sub> = -2.5V	-8.5A
	26mΩ @ V <sub>GS</sub> = -1.8V	-7.2A
	32mΩ @ V <sub>GS</sub> = -1.5V	-6.6A

## Features

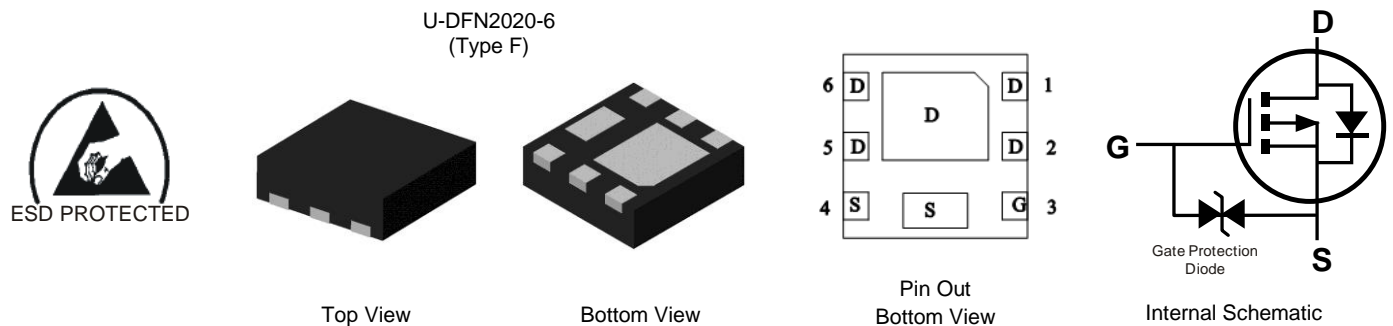
- 0.6mm Profile – Ideal for Low Profile Applications
- PCB Footprint of 4mm<sup>2</sup>
- Low Gate Threshold Voltage
- Fast Switching Speed
- ESD Protected Gate
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](mailto:contact@diodes.com) or your local Diodes representative. <https://www.diodes.com/quality/product-definitions/>**

## Description

This MOSFET is designed specifically for use in battery management applications.

## Mechanical Data

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 **(e4)**
- Weight: 0.0065 grams (Approximate)



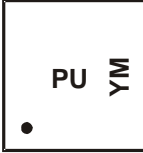
## Ordering Information (Note 4)

Part Number	Case	Packaging
DMP1022UFDF-7	U-DFN2020-6 (Type F)	3,000/Tape & Reel
DMP1022UFDF-13	U-DFN2020-6 (Type F)	10,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information

Site 1

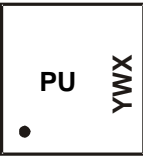


PU = Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year (ex: H = 2020)  
 M = Month (ex: 9 = September)

Date Code Key

Year	2013	...	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	A	...	H	I	J	K	L	M	N	O	P	R
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Site 2



PU = Product Type Marking Code  
 YWX = Date Code Marking  
 Y = Year (ex: 0 = 2020)  
 W = Week (ex: a = Week 27; z Represents Week 52 and 53)  
 X = Internal Code (ex: U = Monday)

Date Code Key

Year	2013	...	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	3	...	0	1	2	3	4	5	6	7	8	9
Week	1-26				27-52				53			
Code	A-Z				a-z				z			
Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat					
Code	T	U	V	W	X	Y	Z					

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	-12	V
Gate-Source Voltage			V <sub>GSS</sub>	±8	V
Continuous Drain Current (Note 6) V <sub>GS</sub> = -4.5V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	-9.5 -7.6	A
	t < 5s	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	-11.0 -8.8	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I <sub>DM</sub>	-90	A
Continuous Source-Drain Diode Current		T <sub>A</sub> = +25°C T <sub>C</sub> = +25°C	I <sub>S</sub>	-2.5 -7.1	A
Pulsed Source-Drain Diode Current (10µs Pulse, Duty Cycle = 1%)			I <sub>SM</sub>	-50	A

**Thermal Characteristics**

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T <sub>A</sub> = +25°C	P <sub>D</sub>	0.73	W
	T <sub>A</sub> = +70°C		0.47	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R <sub>θJA</sub>	172	°C/W
	t < 5s		128	
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	P <sub>D</sub>	2.1	W
	T <sub>A</sub> = +70°C		1.3	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R <sub>θJA</sub>	59	°C/W
	t < 5s		45	
Thermal Resistance, Junction to Case (Note 6)	Steady State	R <sub>θJC</sub>	5.1	
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-12	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250µA
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	—	—	-200	nA	V <sub>DS</sub> = -12V, V <sub>GS</sub> = 0V
Zero Gate Voltage Drain Current T <sub>J</sub> = +55°C (Note 8)	I <sub>DSS</sub>	—	—	-2	µA	V <sub>DS</sub> = -12V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±10	µA	V <sub>GS</sub> = ±8V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-0.35	—	-0.8	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250µA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	12	14.8	mΩ	V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -4A
			15	19		
			20	26		
			23	32		
Diode Forward Voltage	V <sub>SD</sub>	—	-0.8	-1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -8A
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	C <sub>iss</sub>	—	2,712	—	pF	V <sub>DS</sub> = -10V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	514	—		
Reverse Transfer Capacitance	C <sub>rss</sub>	—	467	—		
Gate Resistance	R <sub>g</sub>	—	8.6	18	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge	Q <sub>g</sub>	—	48.3	—	nC	V <sub>GS</sub> = -8V, V <sub>DS</sub> = -6V, I <sub>D</sub> = -10A
Total Gate Charge	Q <sub>g</sub>	—	28.6	—		
Gate-Source Charge	Q <sub>gs</sub>	—	4.2	—		
Gate-Drain Charge	Q <sub>gd</sub>	—	7.0	—		
Turn-On Delay Time	t <sub>D(ON)</sub>	—	25.1	—	ns	V <sub>DS</sub> = -6V, V <sub>GS</sub> = -4.5V, R <sub>G</sub> = 1Ω, I <sub>D</sub> = -8A
Turn-On Rise Time	t <sub>R</sub>	—	39.8	—		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	141	—		
Turn-Off Fall Time	t <sub>F</sub>	—	147	—		

- Notes:
- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
  - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to production testing.

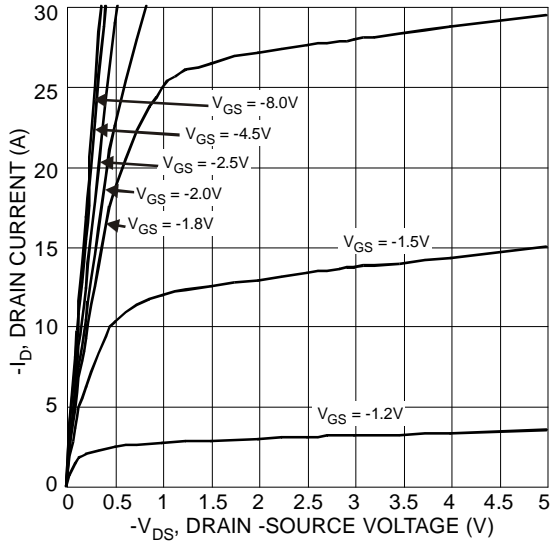


Figure 1 Typical Output Characteristics

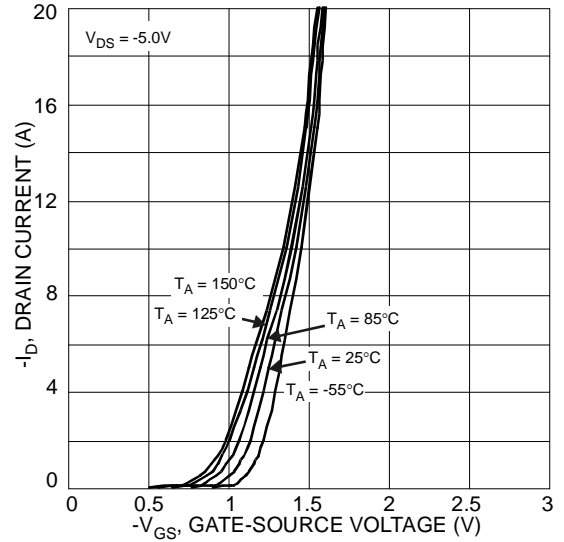


Figure 2 Typical Transfer Characteristics

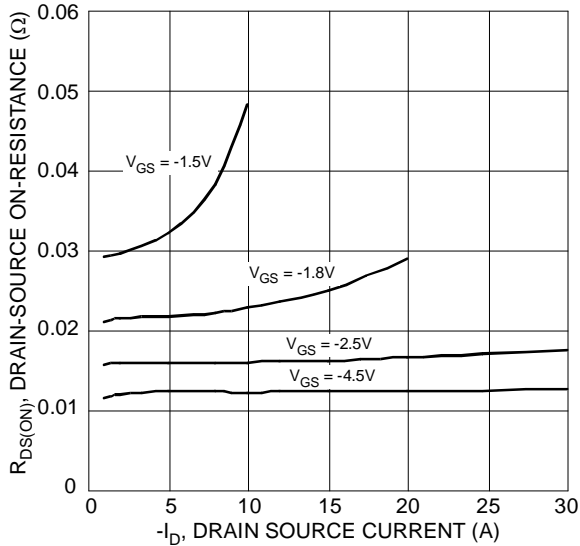


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

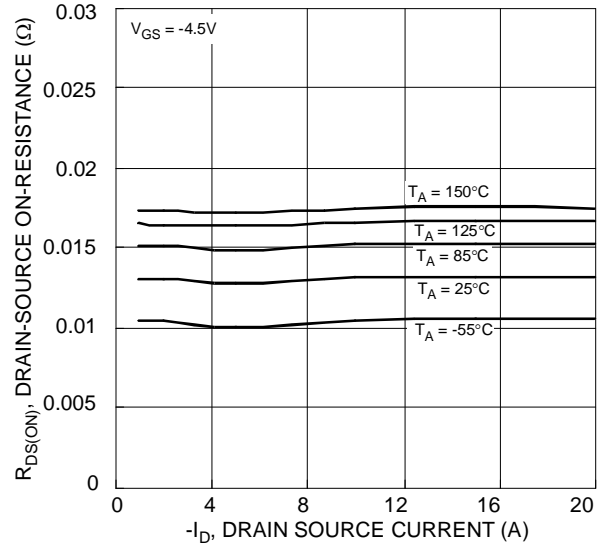


Figure 4 Typical On-Resistance vs. Drain Current and Temperature

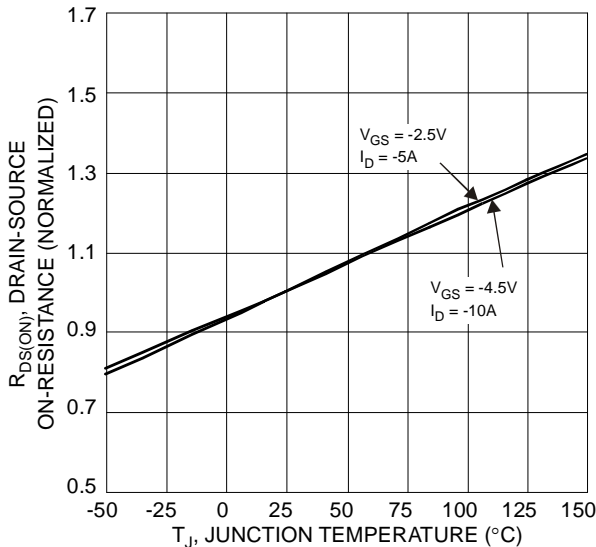


Figure 5 On-Resistance Variation with Temperature

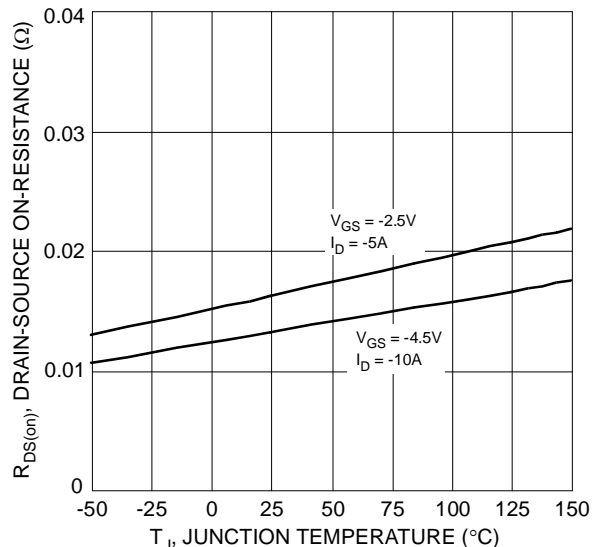


Figure 6 On-Resistance Variation with Temperature

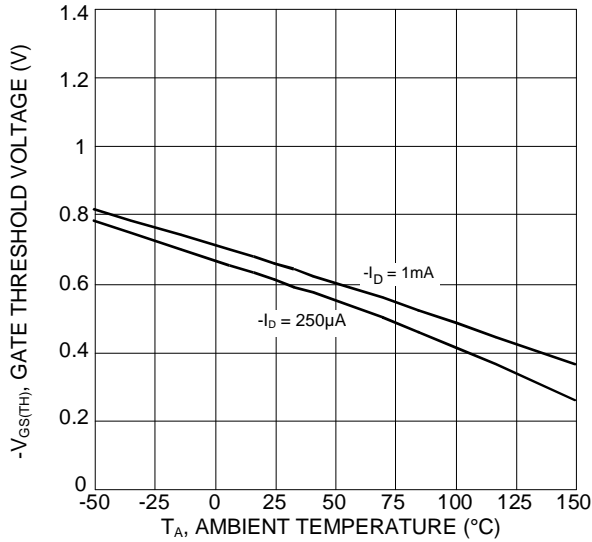


Figure 7 Gate Threshold Variation vs. Ambient Temperature

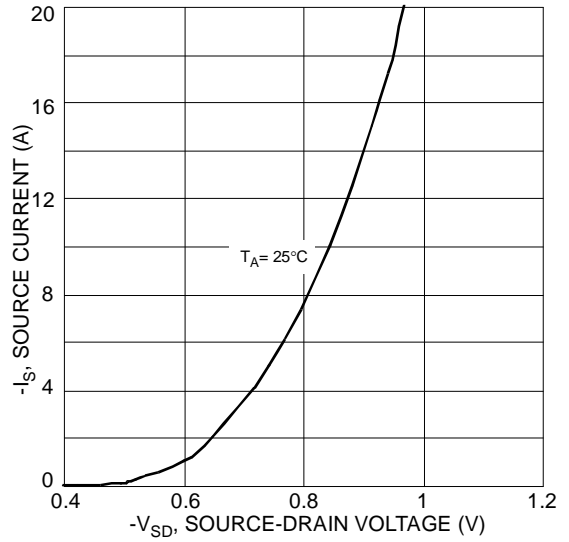


Figure 8 Diode Forward Voltage vs. Current

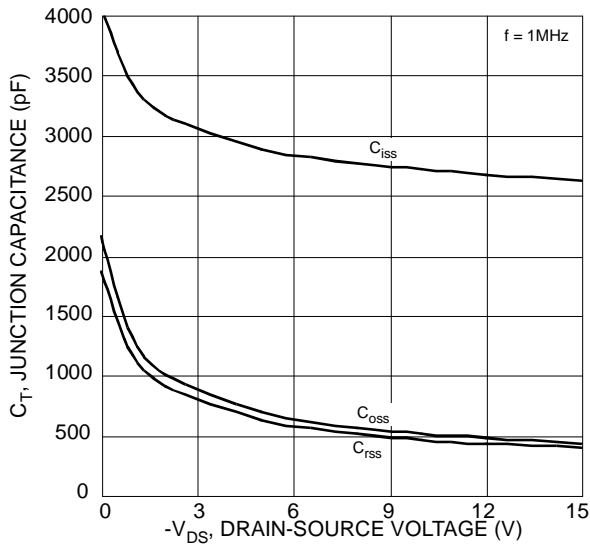


Figure 9 Typical Junction Capacitance

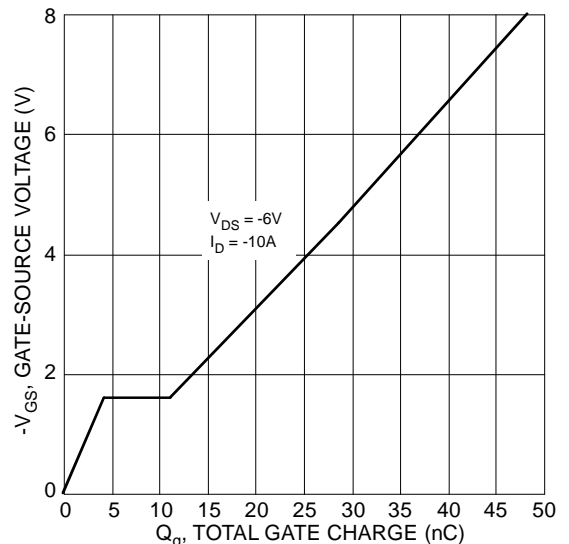


Figure 10 Gate-Charge Characteristics

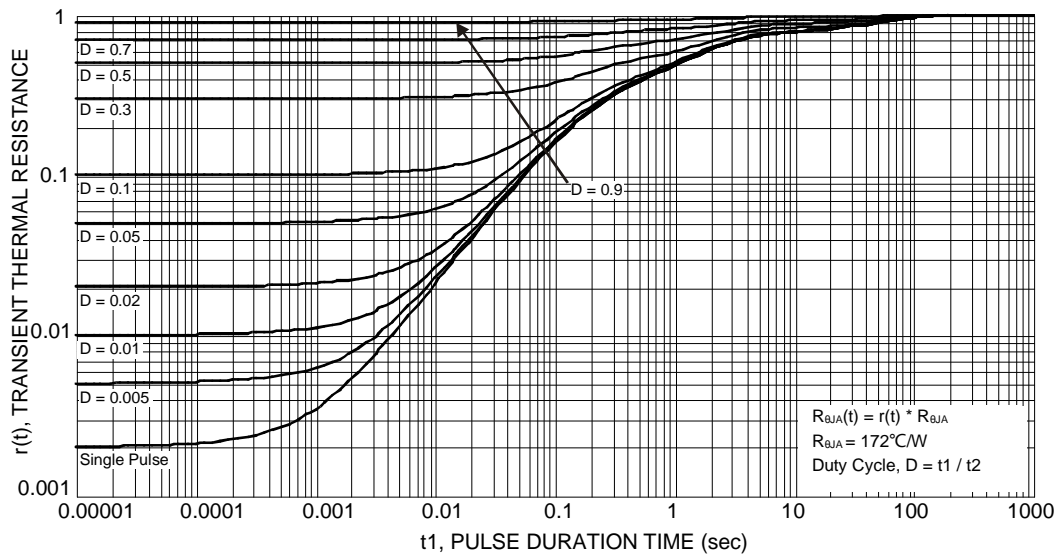


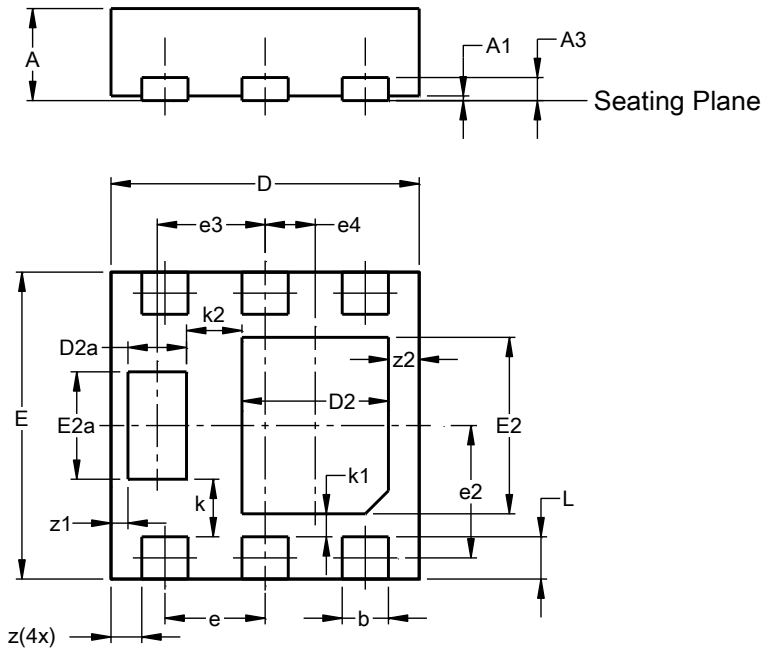
Figure 11 Transient Thermal Resistance

$R_{BJA}(t) = r(t) * R_{BJA}$   
 $R_{BJA} = 172^{\circ}\text{C/W}$   
 Duty Cycle,  $D = t1 / t2$

## Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

U-DFN2020-6 (Type F)

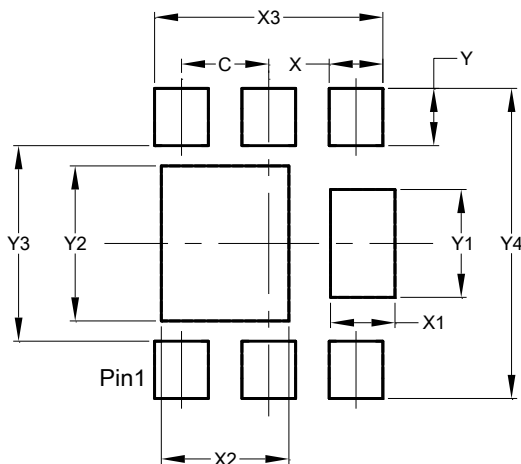


U-DFN2020-6 (Type F)			
Dim	Min	Max	Typ
A	0.57	0.63	0.60
A1	0.00	0.05	0.03
A3	-	-	0.15
b	0.25	0.35	0.30
D	1.95	2.05	2.00
D2	0.85	1.05	0.95
D2a	0.33	0.43	0.38
E	1.95	2.05	2.00
E2	1.05	1.25	1.15
E2a	0.65	0.75	0.70
e	0.65 BSC		
e2	0.863 BSC		
e3	0.70 BSC		
e4	0.325 BSC		
k	0.37 BSC		
k1	0.15 BSC		
k2	0.36 BSC		
L	0.225	0.325	0.275
z	0.20 BSC		
z1	0.110 BSC		
z2	0.20 BSC		
All Dimensions in mm			

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

U-DFN2020-6 (Type F)



Dimensions	Value (in mm)
C	0.650
X	0.400
X1	0.480
X2	0.950
X3	1.700
Y	0.425
Y1	0.800
Y2	1.150
Y3	1.450
Y4	2.300

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